

**Features**

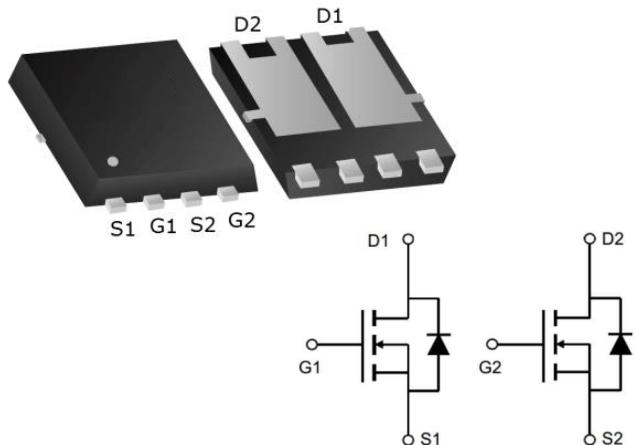
- ★ Split Gate Trench MOS Technology
- ★ 100% EAS Guaranteed
- ★ Fast Switching Speed
- ★ Green Device Available

Product Summary

BVDSS	RDS(ON)	ID
30V	5.5mΩ	45A

Applications

- ★ High Frequency Switching and Synchronous Rectification.
- ★ DC/DC Converter.

PDFN5060-8L Pin Configuration**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	45	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	32	A
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	24	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	20	A
I _{DM}	Pulsed Drain Current ²	135	A
EAS	Single Pulse Avalanche Energy ³	29.8	mJ
I _{AS}	Avalanche Current	27	A
P _D @T _C =25°C	Total Power Dissipation ⁴	30	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	50	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	4.6	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

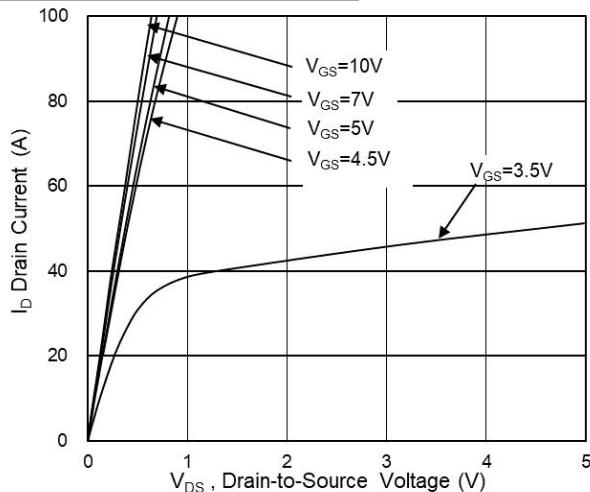
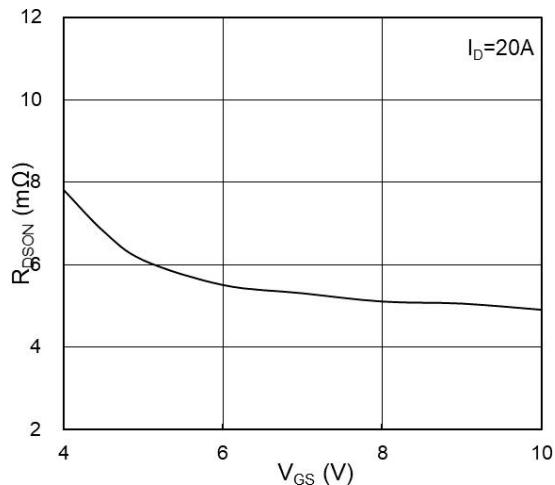
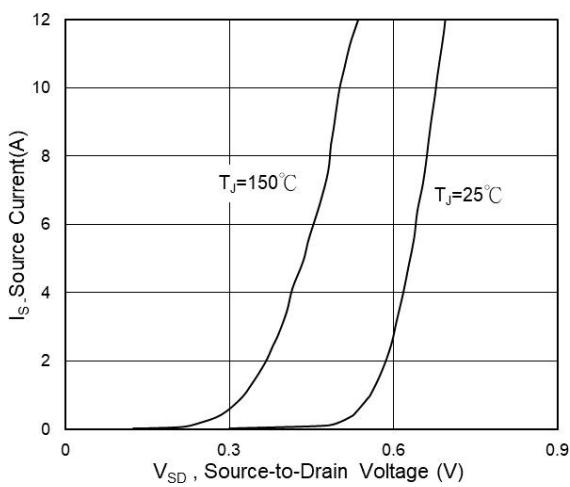
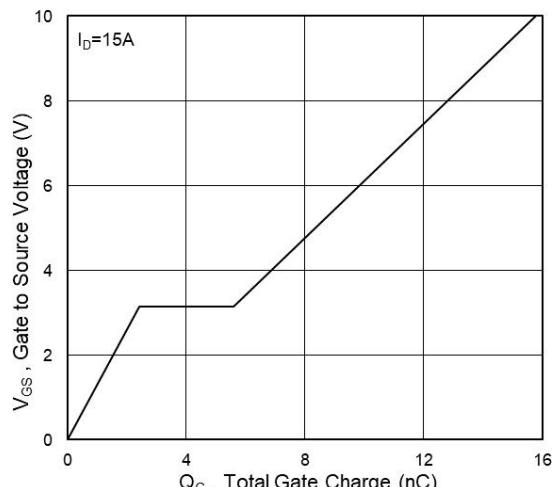
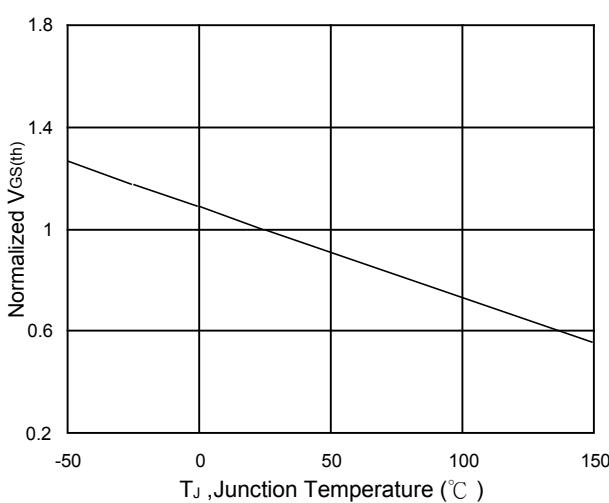
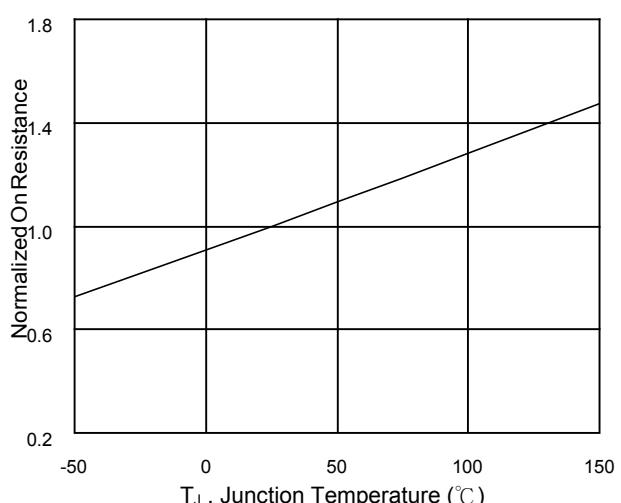
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}$, $\text{I}_D=250\text{\textmu A}$	30	---	---	V
$\text{R}_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$\text{V}_{\text{GS}}=10\text{V}$, $\text{I}_D=20\text{A}$	---	5.5	7.2	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=4.5\text{V}$, $\text{I}_D=15\text{A}$	---	8.5	11	
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{GS}}=\text{V}_{\text{DS}}$, $\text{I}_D=250\text{\textmu A}$	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=24\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$\text{V}_{\text{DS}}=24\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=\pm 20\text{V}$, $\text{V}_{\text{DS}}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$\text{V}_{\text{DS}}=5\text{V}$, $\text{I}_D=20\text{A}$	---	67	---	S
R_g	Gate Resistance	$\text{V}_{\text{DS}}=0\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	$\text{V}_{\text{DS}}=15\text{V}$, $\text{V}_{\text{GS}}=4.5\text{V}$, $\text{I}_D=15\text{A}$	---	8	---	nC
Q_{gs}	Gate-Source Charge		---	2.4	---	
Q_{gd}	Gate-Drain Charge		---	3.2	---	
$\text{T}_{\text{d(on)}}$	Turn-On Delay Time	$\text{V}_{\text{DD}}=15\text{V}$, $\text{V}_{\text{GS}}=10\text{V}$, $\text{R}_g=3.3\Omega$	---	7.1	---	ns
T_r	Rise Time		---	40	---	
$\text{T}_{\text{d(off)}}$	Turn-Off Delay Time		---	15	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	$\text{V}_{\text{DS}}=15\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	814	---	pF
C_{oss}	Output Capacitance		---	498	---	
C_{rss}	Reverse Transfer Capacitance		---	41	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source Current ^{1,6}	$\text{V}_{\text{G}}=\text{V}_{\text{D}}=0\text{V}$, Force Current	---	---	45	A
V_{SD}	Diode Forward Voltage ²	$\text{V}_{\text{GS}}=0\text{V}$, $\text{I}_s=1\text{A}$, $T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$\text{I}_F=20\text{A}$, $d\text{I}/dt=100\text{A}/\mu\text{s}$,	---	15	---	nS
Q_{rr}	Reverse Recovery Charge		$T_J=25^\circ\text{C}$	25	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\text{\textmu s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $\text{V}_{\text{DD}}=25\text{V}$, $\text{V}_{\text{GS}}=10\text{V}$, $\text{L}=0.1\text{mH}$, $\text{I}_{\text{AS}}=24\text{A}$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics**Fig.1 Typical Output Characteristics****Fig.2 On-Resistance vs G-S Voltage****Fig.3 Source Drain Forward Characteristics****Fig.4 Gate-Charge Characteristics****Fig.5 Normalized $V_{GS(th)}$ vs T_J** **Fig.6 Normalized $R_{DS(on)}$ vs T_J**

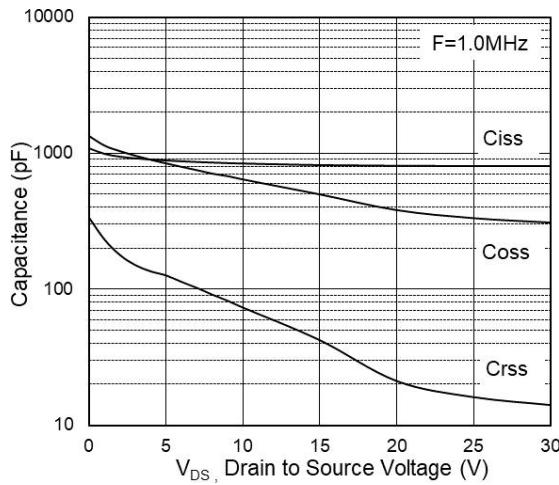


Fig.7 Capacitance

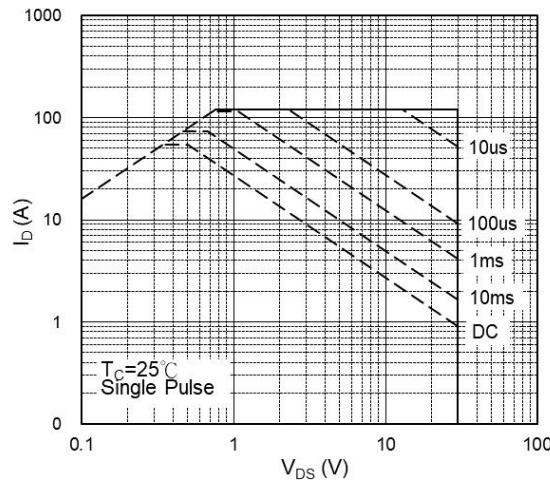


Fig.8 Safe Operating Area

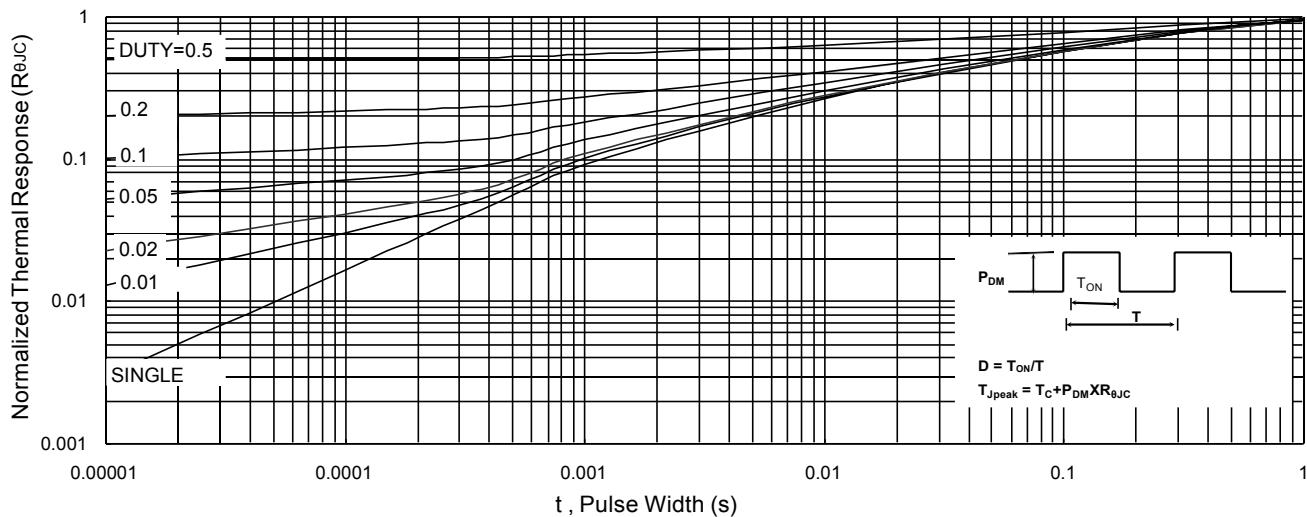


Fig.9 Normalized Maximum Transient Thermal Impedance

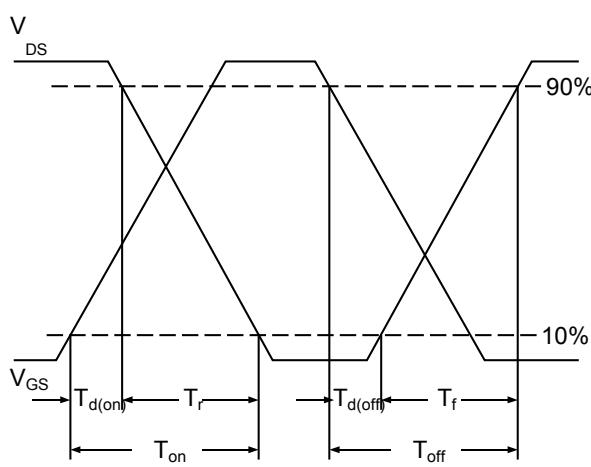


Fig.10 Switching Time Waveform

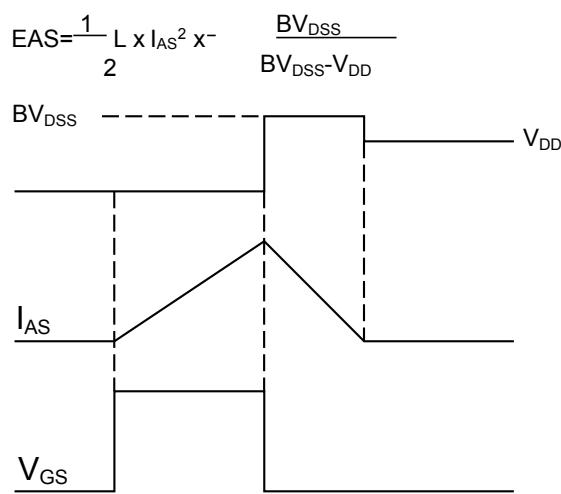
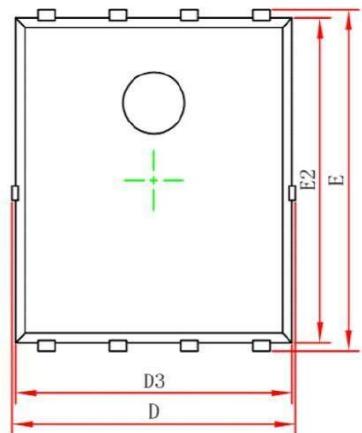
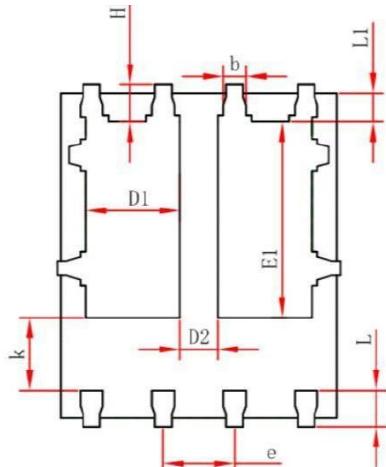
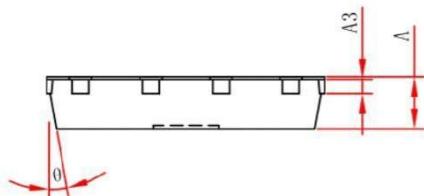


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data- PDFN5X6-8L

Top ViewBottom ViewSide View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.154REF.		0.006REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°